

wherein the thermoplastic material has thermoplastic properties and a thermal expansion coefficient of $6.0 \times 10^{-5} [1/^{\circ}\text{C}]$ or less at a temperature of 80°C to 130°C .

22. (New) A thermoplastic material according to claim 21, wherein a line expansion coefficient is $4.75 \times 10^{-5} [1/^{\circ}\text{C}]$ or less at a temperature of 150°C to 200°C .

23. (New) A thermoplastic material according to claim 21, wherein a line expansion coefficient ratio between a flow direction and a normal direction of the flow direction is 0.55 or more.

24. (New) A thermoplastic material according to claim 21, wherein the thermoplastic material has a bending strength after solidification of 74 MPa or more.

25. (New) A thermoplastic material according to claim 21, wherein an adhesion imparting agent is added to improve adhesion properties to another material by binding with a polar group.

26. (New) A thermoplastic material according to claim 21, further containing silica particles.

27. (New) A thermoplastic material according to claim 21, wherein the thermoplastic material is substantially free of fibrous material.

28. (New) A thermoplastic material according to claim 21, wherein the thermoplastic material is substantially free of thermosetting material.

29. (New) A thermoplastic material according to claim 21, wherein a product obtained by multiplying a value of a line expansion at 25 to 80°C plus a line expansion at 80 to 125°C after solidification, by a bending strength is 25 MPa or less.

30. (New) A thermoplastic material for sealing a semiconductor element, wherein the thermoplastic material has thermoplastic properties and a thermal expansion coefficient of $6.0 \times 10^{-5} [1/^{\circ}\text{C}]$ or less at a temperature of 80°C to 130°C.

31. (New) A process for manufacturing a semiconductor device comprising:
electrically interconnecting a semiconductor element with one end of a
conducting material; and
sealing the semiconductor element and the one end of the conducting material
with a thermoplastic material according to claim 21.

32. (New) A process for manufacturing a semiconductor device comprising:
electrically interconnecting a semiconductor element with one end of a
conducting material; and
sealing the semiconductor element and the one end of the conducting material
with a thermoplastic material according to claim 30.--

REMARKS

Applicants submit this Preliminary Amendment of this continuation application under 37 C.F.R. 1.53(b) and request its entry prior to examination.